





Modeling Coating Thermal Noise at Gravitational Wave Detectors

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Outline

- Introduction
- Methods
- Results
 - Tantala and Titania-doped Tantala
 - Amorphous Silica
- Current Work
- Conclusion



Two-Level System Model

- The Hamiltonian of the TLS system is: $H = H_1 + (V - V_1) = H_2 + (V - V_2),$
 - H_i is the Hamiltonian of isolated well *i*
 - V_i is the potential of well /
- In a localized representation,

$$H = \begin{vmatrix} E_1 + \langle \varphi_1 | V - V_1 | \varphi_1 \rangle & \langle \varphi_1 | H | \varphi_2 \rangle \\ \langle \varphi_2 | H | \varphi_1 \rangle & E_2 + \langle \varphi_2 | V - V_2 | \varphi_2 \end{vmatrix}$$

- where ϕ_i is the harmonic oscillator wave function
- E_i is the harmonic oscillator energy in well *i*



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Two-Level System: Internal Friction

1. K. Gilroy and

 Using the relaxation time approximation, we can calculate the internal friction from the imaginary part of the susceptibility to be

$$Q^{-1} = \frac{1}{(3kT)Y} \iint d\Delta dV \frac{\omega\tau}{1+\omega^2\tau^2} \gamma^2 \left(\frac{\Delta}{E}\right)^2 \operatorname{sech}^2 \left(\frac{E}{2kT}\right) N(\Delta, V)$$

where
• ω is the angular frequency of the wave
• kT is the temperature in eV
• $N(\Delta, V)$ is a number density of TLS's
• γ is the mechanical dipole
• τ is the relaxation time
• Y is the Young's modulus for the system
• W Phillips, Philosophical Magazine B 43,735 (1981)

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LIGO-G1601068

classical MD



Classical Molecular Dynamics

- Uses Newtonian dynamics to update atomic positions
- Interatomic potentials are modeled to fit experimental data
 - Density
 - Elastic moduli
 - Radial distribution functions
 - Formation energy
- Allows simulations of millions of atoms at low computational cost

$$V_{1-2}(r) = Ae^{-Br} - \frac{C}{r^6} + \frac{kq_1q_2}{r^2}$$



Distance (Å)

https://en.wikipedia.org/wiki/Buckingham_potential



Method Overview



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Internal Friction

- Calculated Q⁻¹ overestimates measured Q⁻¹ by a factor of 2.5, but the trends and shape of Q⁻¹(T) follow experiment
- Percent changes of peak Q⁻¹(T) match experiment quite closely
- For low-T Q⁻¹, optimal value of titaniadoping is 62%
- Room-temperature Q⁻¹ shows nonmonotonic behavior with Ti-doping, but agree with decrease seen in 14% doped experiment







Calculated Q⁻¹ Parameters



- Ti doping generally corresponds with
 - shorter relaxation time (au_0)
 - larger Young's modulus (Y)
 - weaker longitudinal coupling constant (γ)
- The minimum in γ leads to the optimal doping at 64%
- Controlling the coupling constant through doping is a way to decrease $Q^{\text{-}1}$



TLS Activation

- Regions of Q⁻¹(T) can be connected to TLS's by plotting the expression for Q⁻¹ without integrating over V and Δ
- This identifies transitions that lead to loss at a particular temperatures





Statistics of TLS transitions



- Sharper peaks in the number of atoms involved in TiO₂ compared to Ta₂O₅ suggest a more localized transition
- Similar statistics \rightarrow similar loss mechanism



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Previous calculations gave good agreement for low temperature peak

3. R. Hamdan, J. P. Trinastic, and H. Cheng, The Journal of chemical physics 141, 054501 (2014).



Re-examining Amorphous Silica



behavior well! Why?

3. R. Hamdan, J. P. Trinastic, and H. Cheng, The Journal of chemical physics 141, 054501 (2014).

4. I. Martin, R. Nawrodt, K. Craig, C. Schwarz, R. Bassiri, G. Harry, J. Hough, S. Penn, S. Reid, R. Robie, et al., Classical and Quantum Gravity 31, 035019 (2014).

- Separated distribution gives opposite behavior of the correlated distribution
- Separated distribution has high density below $V < 2\Delta$, violating the definition of a TLS

Internal Friction

- $N_{sep}(V, \Delta)$ does not compare well at all to experiment
- $N_{cut}(V, \Delta)$ agrees with low temperature peak
- $N_{corr}(V, \Delta)$ agrees with IBS low temperature peak and second peak around 150K

Statistics of Atomic Transitions

c) Oxygen Rotations

- Features have well-defined distributions
- This suggests the features are due to distinct transitions

Atomic Transitions

Low Temperature Peak (20 K)

Second Peak

(120 K)

Minimum 1

Both Minima LIGO-G1601068

Minimum 2

Current and Future Work

- New implementation within LAMMPS
 - More options, will improve accuracy of au_0 and γ
 - More user-friendly interface facilitates collaboration
- Expanding frequency-dependence of the model, but calculating relaxation time for each TLS
- Density-dependent study of amorphous SiO₂
- Calculating loss of Si-doped tantala and Zr-doped tantala
- Recruited two new students!

3. R. Hamdan, J. P. Trinastic, and H. Cheng, The Journal of chemical physics 141, 054501 (2014).

4. I. Martin, R. Nawrodt, K. Craig, C. Schwarz, R. Bassiri, G. Harry, J. Hough, S. Penn, S. Reid, R. Robie, et al., Classical and Quantum Gravity 31, 035019 (2014).

Conclusion

- Using classical MD to provide inputs for a TLS model gives good agreement with internal friction measurements in amorphous oxides
- This model allows us to
 - Screen materials by predict effect of doping on the internal friction
 - Understand the atomic transitions that cause internal friction and thermal noise
- The implementation in LAMMPS offers **fast, user-friendly** calculations of the internal friction in amorphous oxides

TLS Distributions

- To facilitate analytical calculations and improve the rate of convergence, previous studies have separated that number density: $N_{sep}(V, \Delta) = f(\Delta)g(V)$
- To improve comparison to experiment, some work also introduces a cut-off for TLS's with Δ above 0.1 eV.

$$N_{cut}(V,\Delta) = f(\Delta)g(V)\Theta(\Delta_{cut} - \Delta)$$

• We compare the results of these two distributions with the correlated distribution, $N_{corr}(V, \Delta)$.

Two-Level System States

- We can diagonalize this Hamiltonian, and we obtain two states with $\frac{\pm E}{2} = \pm \frac{1}{2} \sqrt{\Delta^{2} + \Delta_{0}^{2}}:$ $\frac{\psi_{1} = \varphi_{1} cos\theta + \varphi_{2} sin\theta}{\psi_{2} = \varphi_{1} sin\theta - \varphi_{2} cos\theta}$ Where $\tan(2\theta) = \frac{\Delta_{0}}{\Lambda}$.
- The dipole moments of each state are

$$p = \pm p_0 \frac{\Delta}{E}$$

where p_0 is the dipole moment of the isolated state ($\Delta \gg \Delta_0$).

The TLS model in MD

System trajectory

ξ2

Rashid Hamdan, unpublished.

- The barrier search moves the system through the potential energy landscape
- This method is repeated tens to hundreds of thousands of times to get a TLS distribution
- The average relaxation time and average coupling constant is calculated from a subset of the discovered TLS's

Results: TLS Density

Model Inputs: Elastic Moduli and Coupling

- Young's modulus
 - $\sigma_i = c_{ij}\varepsilon_i$
 - Strain the system to determine what the elastic moduli are
- Coupling Constant

•
$$\gamma_j = 1/2 \frac{\partial \Delta}{\partial u_j}$$

• The asymmetry changes as unit cell is strained, which is the coupling to mechanical field.

Model Inputs: Relaxation Time

• The relaxation time is calculated using the Arrhenius law:

$$\tau = \tau_0 e^{\frac{V}{kT}} \operatorname{sech}(\frac{\Delta}{2kT})$$

• τ_0 is the inverse attempt frequency. This value is calculated by $\tau_0^{-1} = \frac{\prod_{i=1}^{3N} v_i^0}{\prod_{i=1}^{3N} v_i^s} e^{S/k}$

where v_i^0 and v_i^s are the vibrational frequencies at the minimum and saddle point respectively, and the exponential factor is due to entropy

